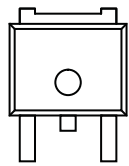


Automotive N-Channel 55 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	55
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.020
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.026
I_D (A)	30
Configuration	Single

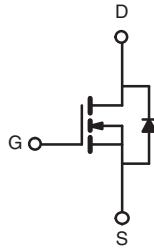
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- Compliant to RoHS Directive 2002/95/EC


TO-252


Top View

Drain Connected to Tab



N-Channel MOSFET

ORDERING INFORMATION

Package	TO-252
Lead (Pb)-free and Halogen-free	SQD30N05-20L-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C ^a	30
		$T_C = 125$ °C	19
Continuous Source Current (Diode Conduction) ^a	I_S	30	A
Pulsed Drain Current ^b	I_{DM}	120	
Single Pulse Avalanche Energy	E_{AS}	20	
Single Pulse Avalanche Current	I_{AS}	20	mJ
Maximum Power Dissipation ^b			
		$T_C = 125$ °C	16
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	60	°C/W
Junction-to-Case (Drain)	R_{thJC}	3.0	

Notes

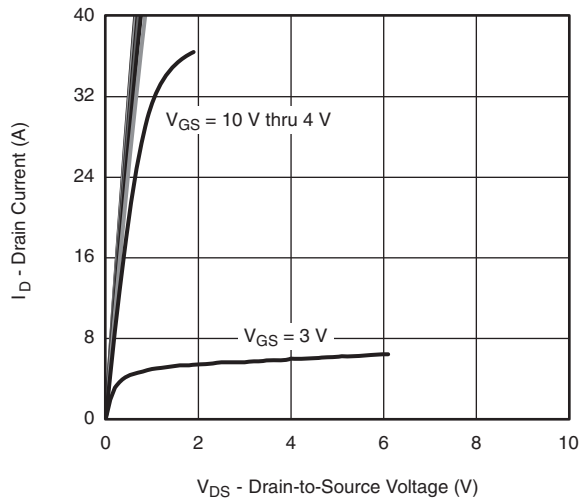
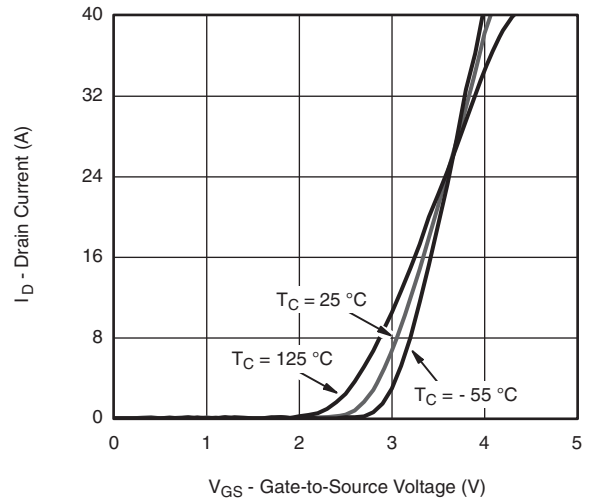
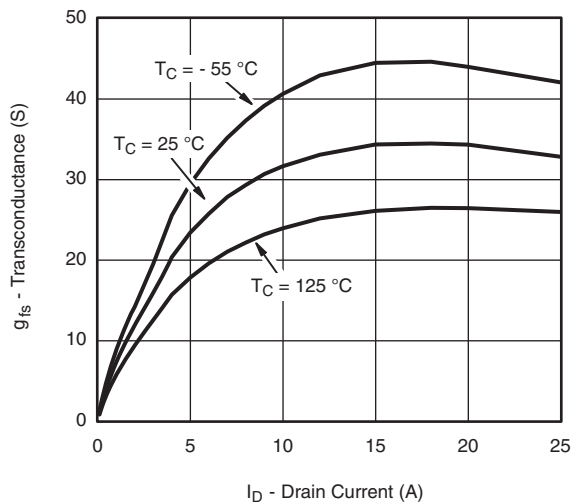
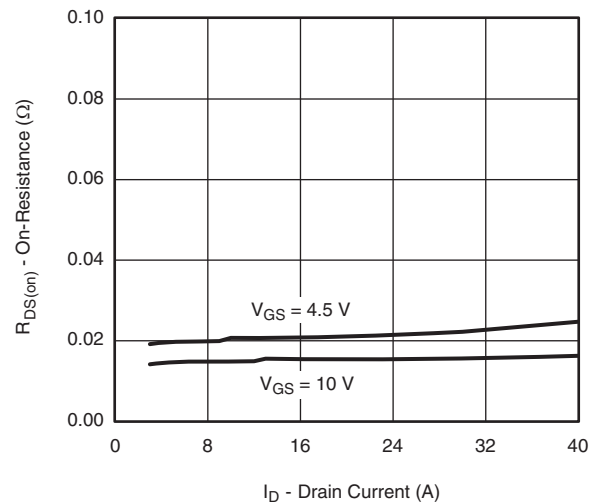
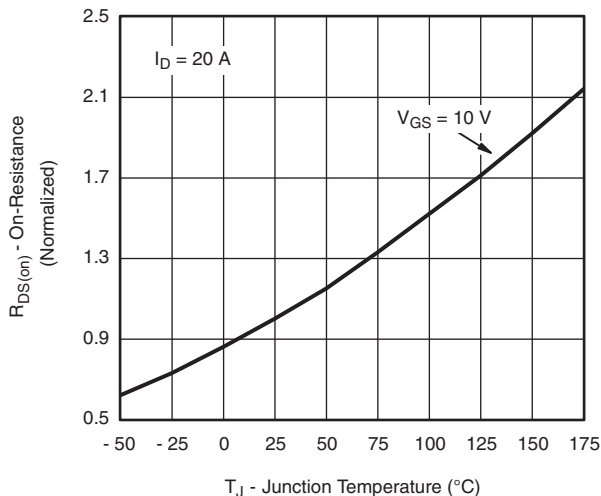
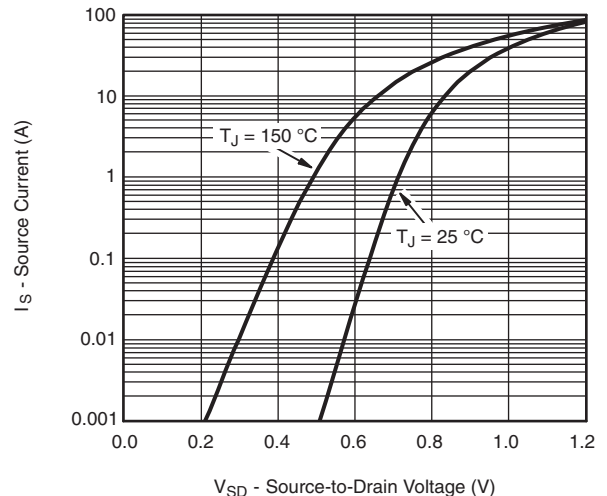
- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		55	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.5	2.0	2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 55\text{ V}$	-	-	1.0	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = 55\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 55\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 5\text{ V}$	$V_{DS} \geq 5\text{ V}$	30	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	-	0.016	0.020	Ω
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	-	0.035	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	-	0.043	
		$V_{GS} = 4.5\text{ V}$	$I_D = 15\text{ A}$	-	0.021	0.026	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		-	34	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	-	938	1175	μF
Output Capacitance	C_{oss}			-	203	255	
Reverse Transfer Capacitance	C_{rss}			-	86	110	
Total Gate Charge ^c	Q_g	$V_{GS} = 5\text{ V}$	$V_{DS} = 25\text{ V}, I_D = 35\text{ A}$	-	12	18	nC
Gate-Source Charge ^c	Q_{gs}			-	4.1	-	
Gate-Drain Charge ^c	Q_{gd}			-	4.8	-	
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 25\text{ V}, R_L = 0.71\text{ }\Omega$ $I_D \cong 35\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		-	7	11	ns
Rise Time ^c	t_r			-	10	15	
Turn-Off Delay Time ^c	$t_{d(off)}$			-	18	27	
Fall Time ^c	t_f			-	5	8	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	120	A
Forward Voltage	V_{SD}	$I_F = 80\text{ A}, V_{GS} = 0\text{ V}$		-	1.2	1.5	V

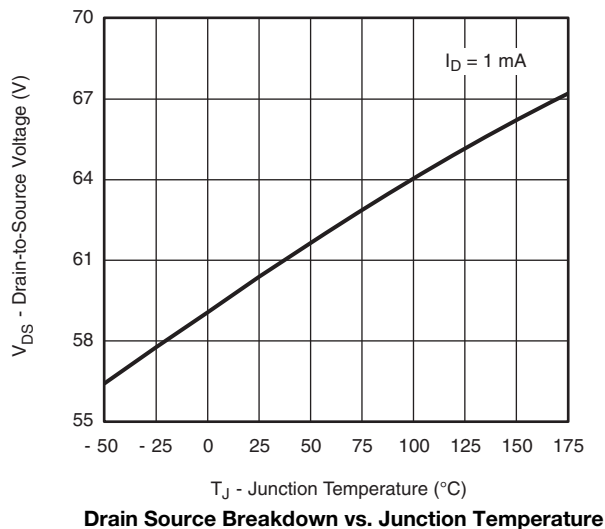
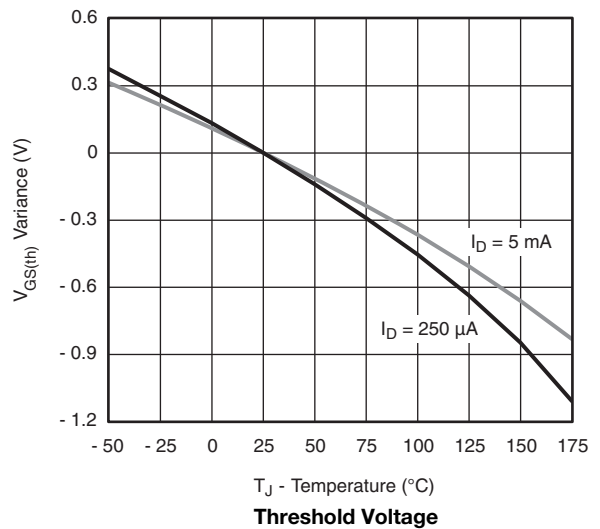
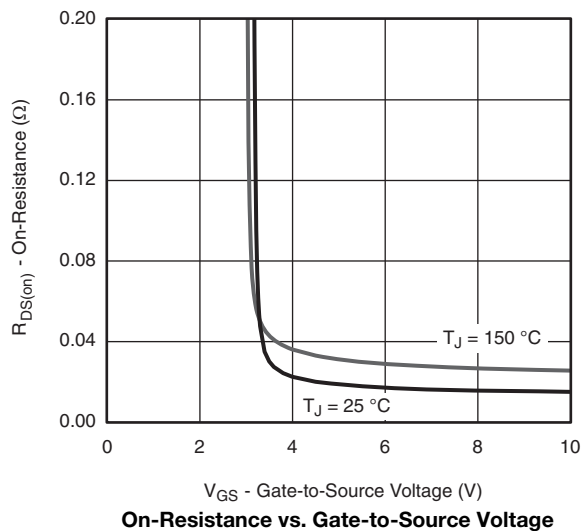
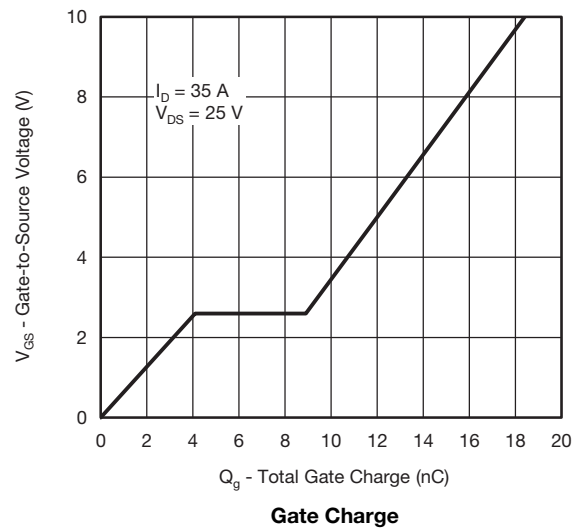
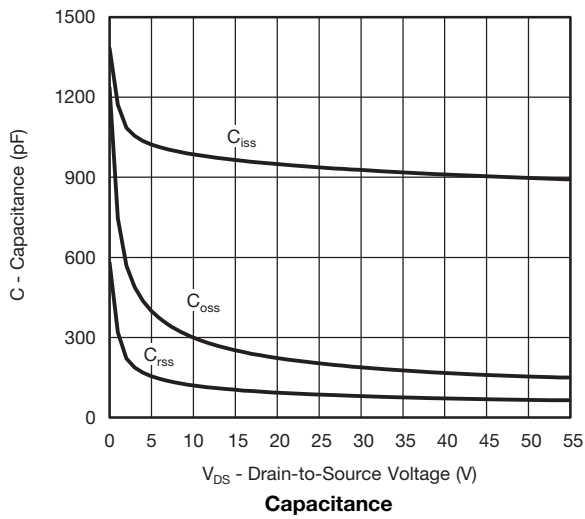
Notes

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

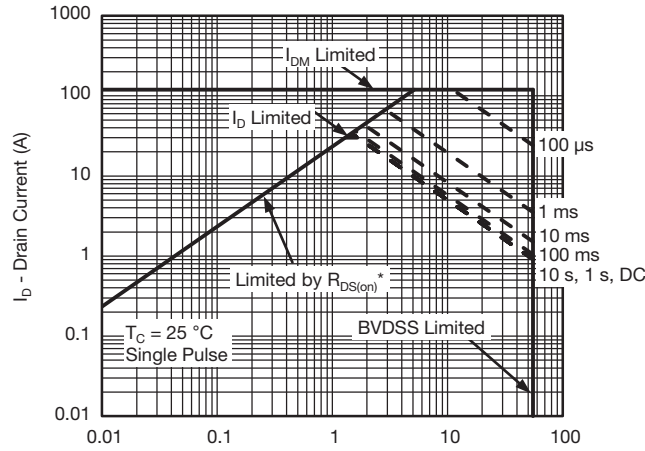
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

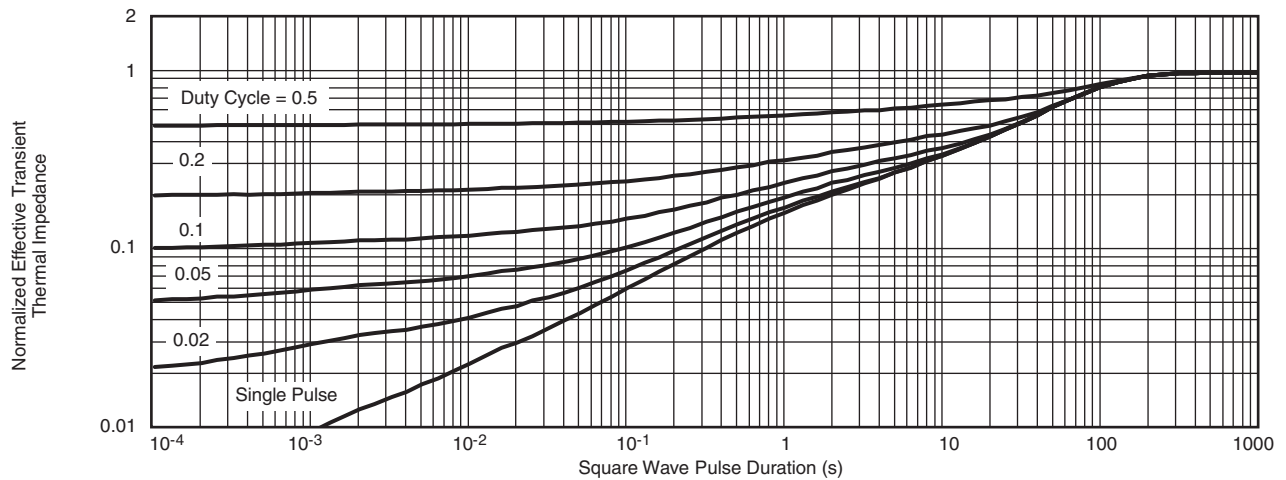


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



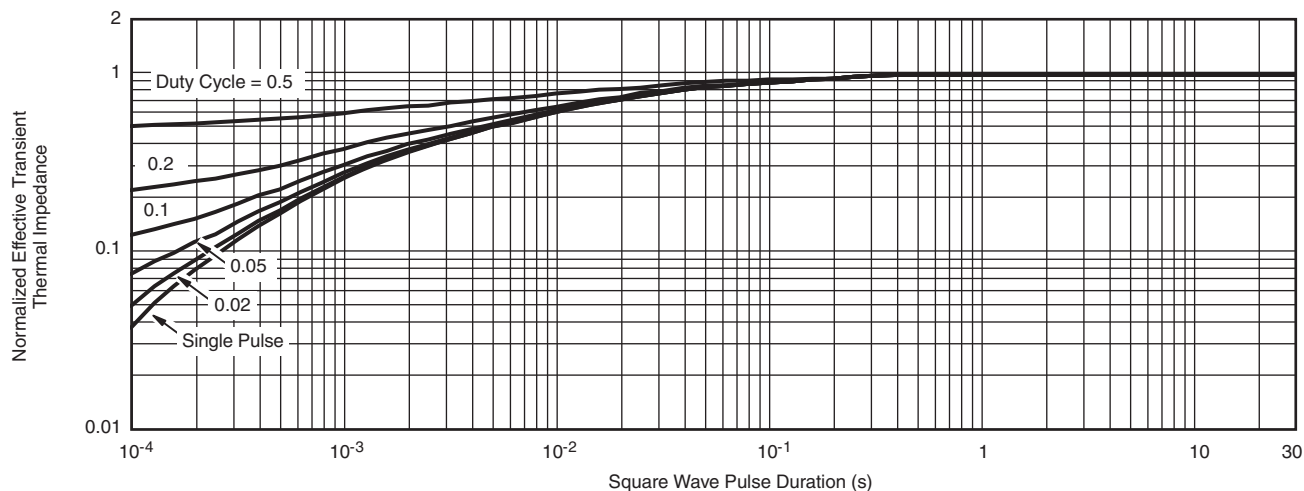
V_{DS} - Drain-to-Source Voltage (V)
 * $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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